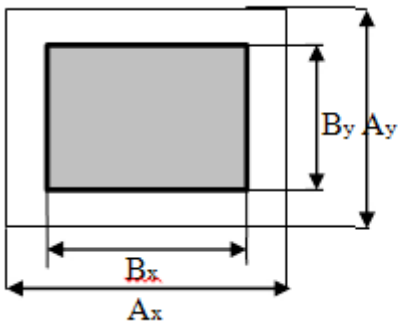

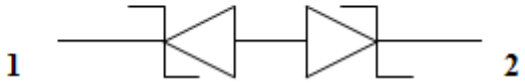

Mechanical data: A_x=A_y=280um
Chip thickness: 635 +/-20um
Scribe Line width - 45um.
Top Metal: Ti-Ni-Ag for Soldering.
Back side : without metallization
Top Side - pin 1, **Back Side** - pin 2.
Probing: sampling testing: no bad dice inking, guaranteed good dice quantity≥95%.

Schematic and pinning diagram

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Working Peak Reverse Voltage	V_{RWM}		5,0.	V
Peak Pulse Power	P_{pp}	t_p= 8/20uS	85*	W
Peak Pulse Current	I_{pp}	t_p= 8/20uS	5,0*	A
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4.	+/-18,0 (Contact); +/-18,0 (Air).	kV
Max.junction temperature	T_j		+150	ºC

Characteristics **(Ta=25ºC)**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_R	Diode reverse leakage current.	V=±5 V	-	-	100	nA
V_{BR}	Breakdown voltage. Pin1 to 2 and Pin 2 to 1	I_R=1mA	5,6	-	9,4	V
C_j	Diode capacitance .	f=1MHz, V_{dc}=0 V.	8,0	10	13,0	pF
V_{CL}	Clamping Voltage	I_{pp}=1,0A; I_{pp}= 5,0A; t_p= 8/20uS .	- -	- -	9,0* 17,0*	V

*- For Device testing